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## CHARGE COUPLED ELEMENT TYPE SOLID IMAGING DEVICE OF OVERFLOW DRAIN STRUCTURE

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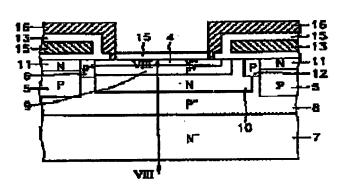
US5619049 (A1)

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## Abstract of JP7050402

PURPOSE: To provide a charge-coupled device type solid state image-pickup device, in which an overflow drain to which an impurity of high concentration has been doped is formed on each optical diode. CONSTITUTION: An impurity layer of high concentration is formed in an uppermost layer 9 of a PNPN structure and is used as an overflow drain 4. Consequently, overflow operation and electronic shutter operation can be performed with a low voltage, and an on-chip circuit of a solid-state image-pickup device can be realized.



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